

SANYO

No.866C

2SC3000

NPN Epitaxial Planar Silicon Transistor

HF Amp Applications**Features**

- . FBET series.
- . High f_T and small c_{re} .

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

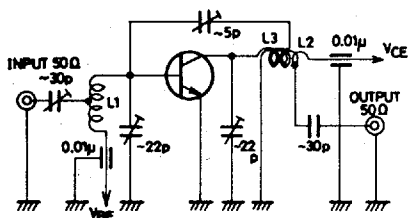
			unit
Collector to Base Voltage	V_{CB0}	30	V
Collector to Emitter Voltage	V_{CE0}	20	V
Emitter to Base Voltage	V_{EB0}	5	V
Collector Current	I_C	30	mA
Collector Dissipation	P_C	250	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=10\text{V}, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EB0}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=6\text{V}, I_C=1\text{mA}$	60*		320*	
Gain Bandwidth Product	f_T	$V_{CE}=6\text{V}, I_C=1\text{mA}$	200	320		MHz
Reverse Transfer Capacitance	c_{re}	$V_{CB}=6\text{V}, f=1\text{MHz}$	0.7	1.1	1.4	pF
Base to Collector Time Constant	$r_{bb}'C_c$	$V_{CB}=6\text{V}, I_C=1\text{mA}, f=31.9\text{MHz}$		15	22	ps
Noise Figure	NF	$V_{CE}=6\text{V}, I_C=1\text{mA}, f=100\text{MHz}$		3.0		dB
Power Gain	PG	$V_{CE}=6\text{V}, I_C=1\text{mA}, f=100\text{MHz}$		25		dB

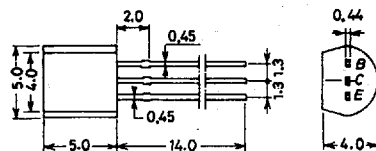
*:The 2SC3000 is classified by 1mA h_{FE} as follows :

60	D	120	100	E	200	160	F	320
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NF, PG Test Circuit

Unit(Capacitance: F)

- L1: 1mm ϕ plated wire, 10mm ϕ 5T, tapped at 2T from V_{BE} .
 L2: 1mm ϕ plated wire, 10mm ϕ 7T, tapped at 1T from V_{CE} .
 L3: 1mm ϕ enameled wire, 10mm ϕ 3T.

Case Outline 2003A (unit:mm)

JEDEC: TO-92
 EIAJ: SC-43
 SANYO: NP

B: Base
 C: Collector
 E: Emitter

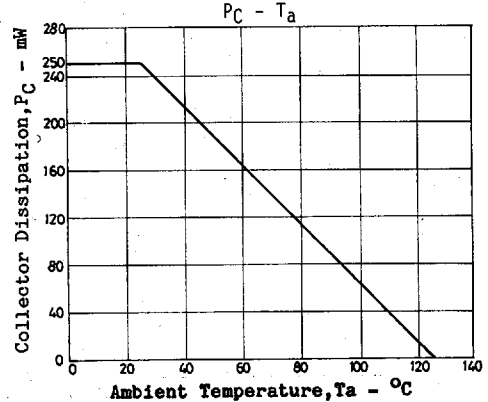
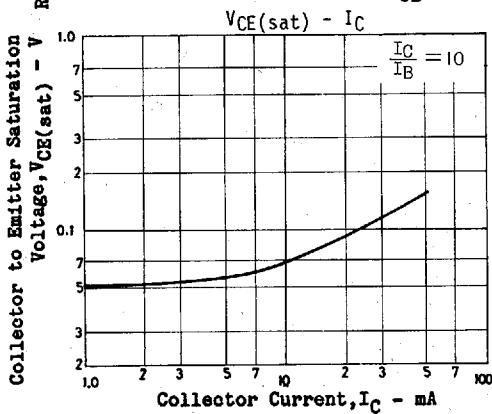
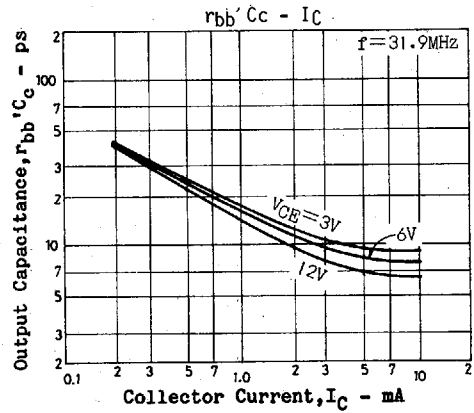
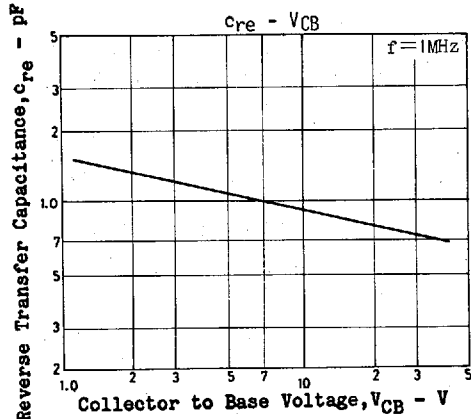
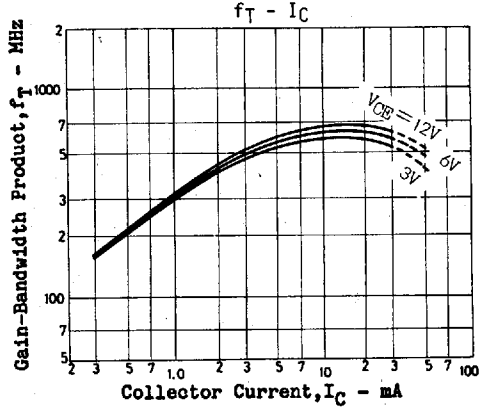
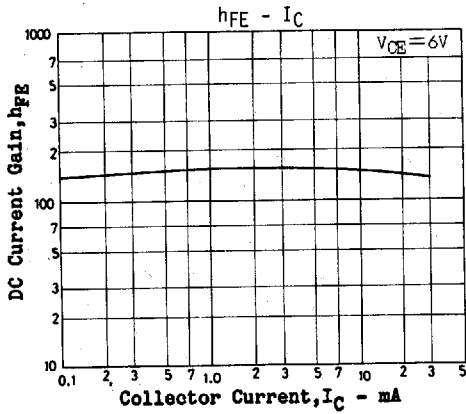
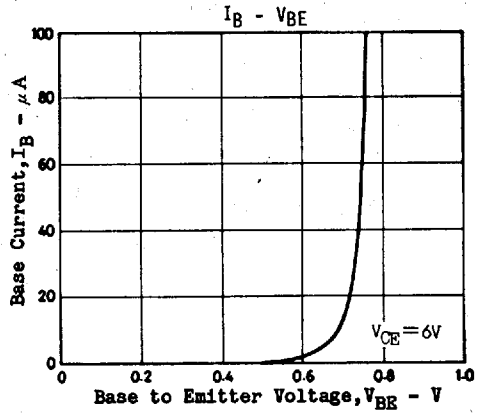
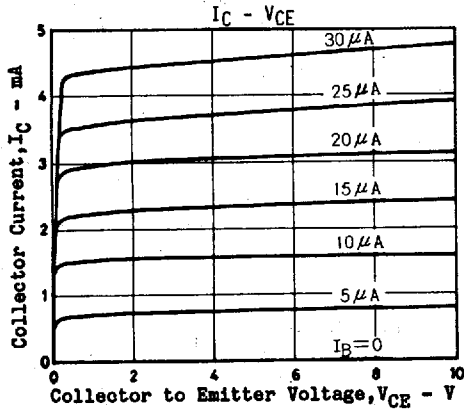
Specifications and information herein are subject to change without notice.

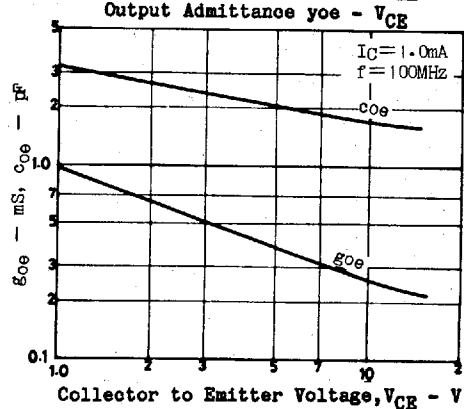
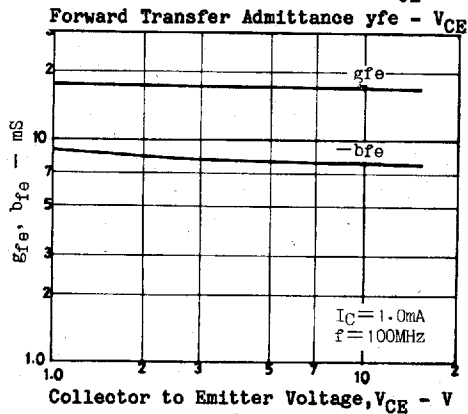
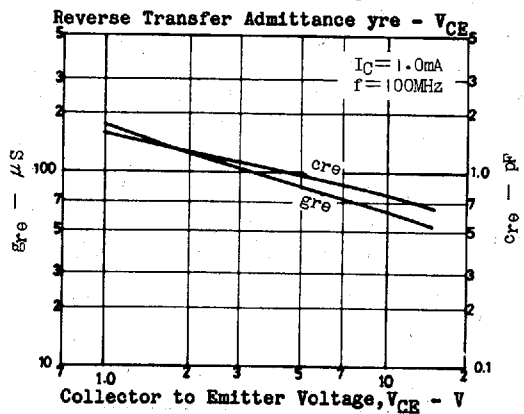
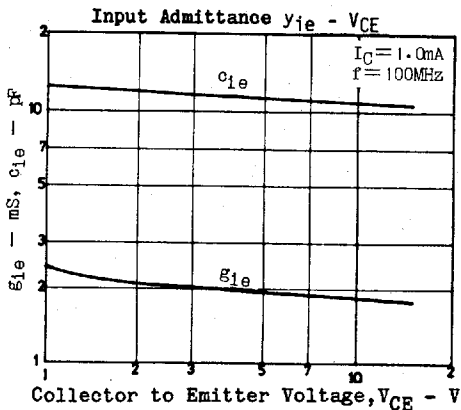
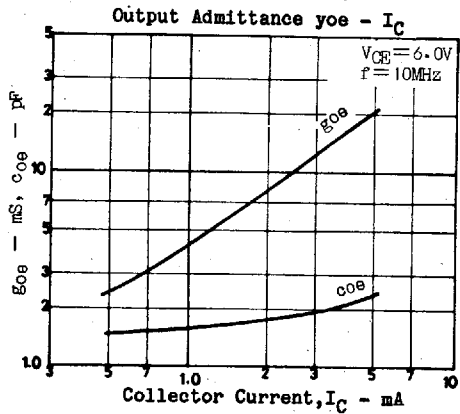
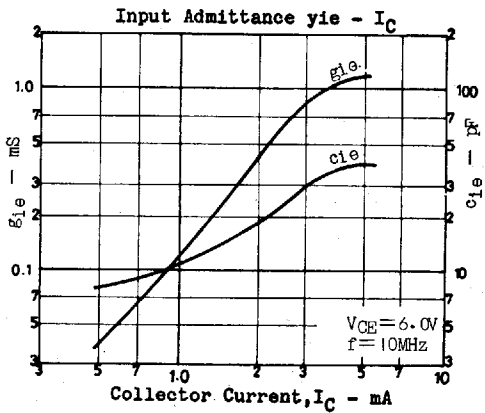
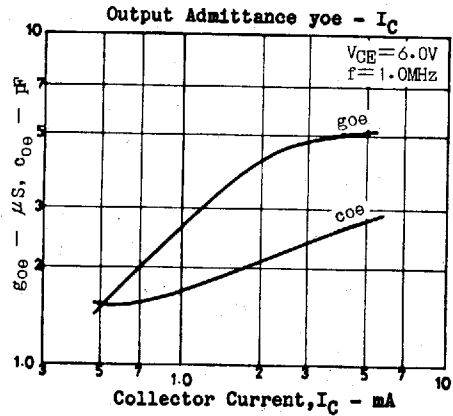
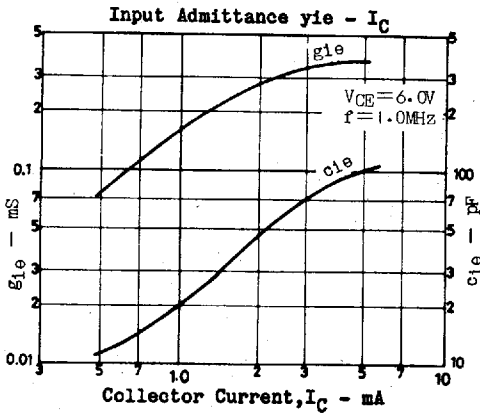
SANYO Electric Co., Ltd. Semiconductor Business Headquarters

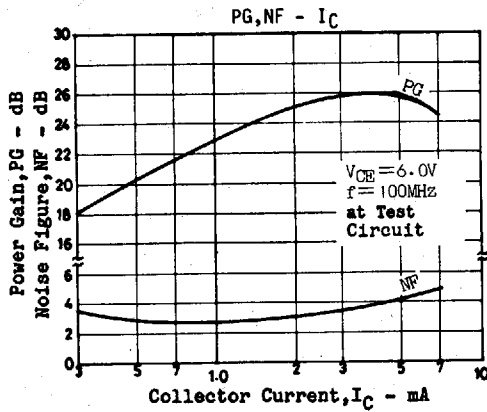
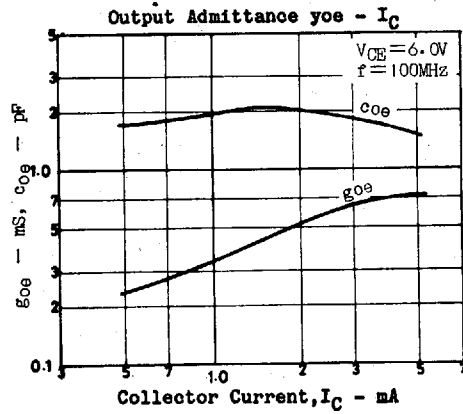
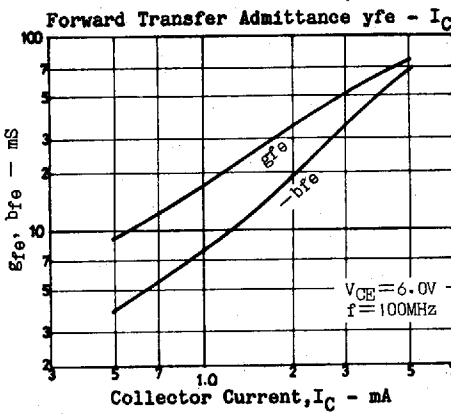
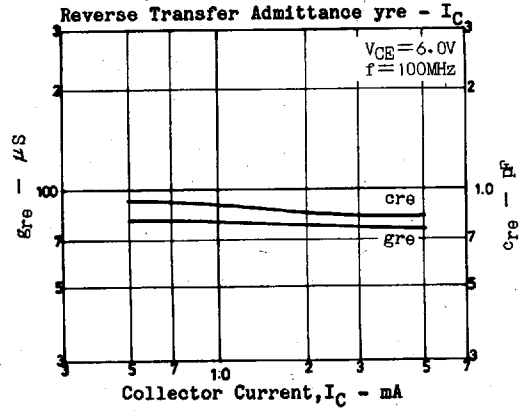
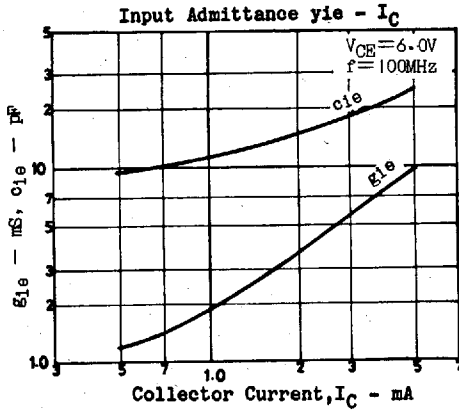
TOKYO OFFICE Tokyo Bldg. 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

4147KI/3125MW, TS No.866-1/4

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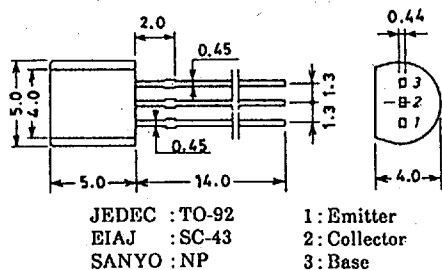




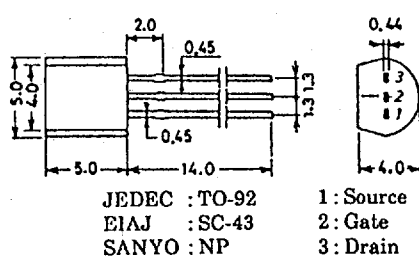
CASE OUTLINES OF LEAD FORMED SMALL SIGNAL TRANSISTORS

- All of Sanyo lead formed small signal transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

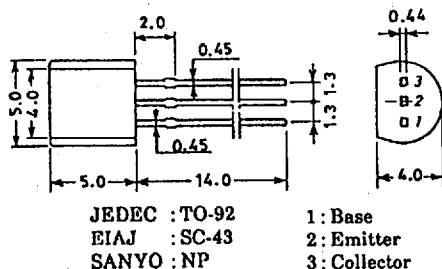
Case Outline 2003A/2003B (unit : mm)



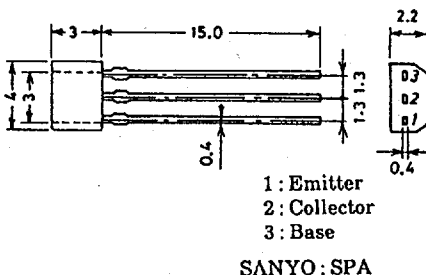
Case Outline 2019A/2019B (unit : mm)



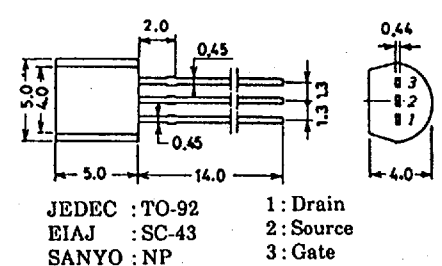
Case Outline 2004A (unit : mm)



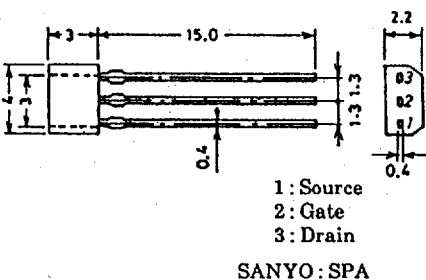
Case Outline 2033 (unit : mm)



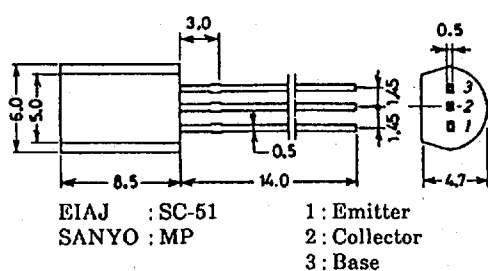
Case Outline 2005A (unit : mm)



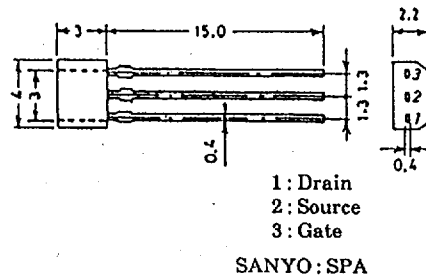
Case Outline 2034/2034A (unit : mm)



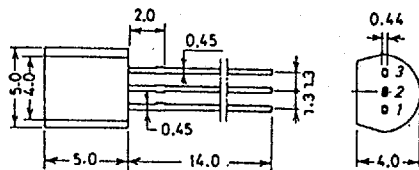
Case Outline 2006A (unit : mm)



Case Outline 2040 (unit : mm)



Case Outline 2061 (unit : mm)



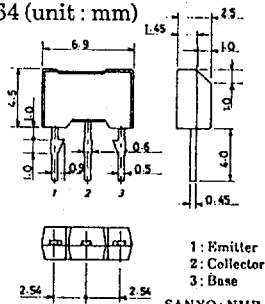
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EIAJ : SC-43

SANYO : NP

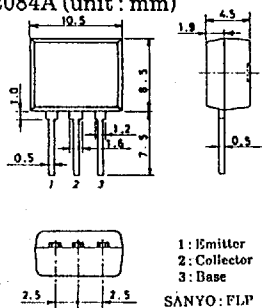
- 1: Emitter
- 2: Base
- 3: Collector

Case Outline 2064 (unit : mm)



- 1: Emitter
 - 2: Collector
 - 3: Base
- SANYO : NMP

Case Outline 2084A (unit : mm)



- 1: Emitter
 - 2: Collector
 - 3: Base
- SANYO : FLIP